

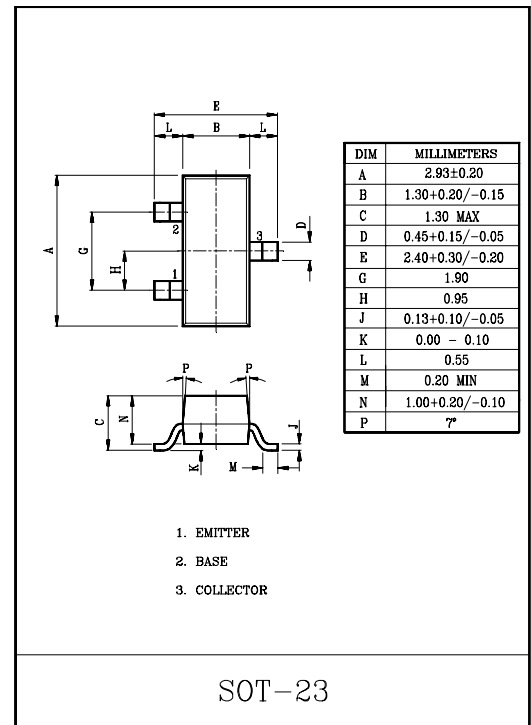
GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

• For Complementary with NPN Type BC849/850

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage	BC859	V_{CBO}	-30	V
	BC860		-50	
Collector-Emitter Voltage	BC859	V_{CEO}	-30	V
	BC860		-45	
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Current		I_C	-100	mA
Collector Power Dissipation		P_C *	350	mW
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55~150	℃

P_C * : Package Mounted On 99.5% Alumina 10×8×0.6mm.



ELECTRICAL CHARACTERISTICS (Ta=25℃)

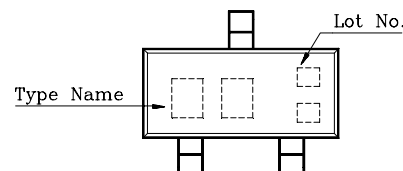
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	BC859	$V_{(BR)CEO}$ $I_C=-10mA, I_B=0$	-30	-	-	V
	BC860		-45	-	-	
Collector-Base Breakdown Voltage	BC859	$V_{(BR)CBO}$ $I_C=-10\mu A, I_E=0$	-30	-	-	V
	BC860		-50	-	-	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB}=-30V, I_E=0$	-	-	-15	nA
DC Current Gain	h_{FE}	$I_C=-2mA, V_{CE}=-5V$	125	-	475	
Base-Emitter Voltage	$V_{BE(ON) 1}$	$I_C=-2mA, V_{CE}=-5V$	-0.6	-0.65	-0.75	V
	$V_{BE(ON) 2}$	$I_C=-10mA, V_{CE}=-5V$	-	-	-0.82	
Collector-Emitter Saturation Voltage	$V_{CE(sat) 1}$	$I_C=-10mA, I_B=-0.5mA$	-	-0.075	-0.3	V
	$V_{CE(sat) 2}$	$I_C=-100mA, I_B=-5mA$	-	-0.25	-0.65	
Base-Emitter Saturation Voltage	$V_{BE(sat) 1}$	$I_C=-10mA, I_B=-0.5mA$	-	-0.7	-	V
	$V_{BE(sat) 2}$	$I_C=-100mA, I_B=-5mA$	-	-0.85	-	
Transition Frequency	f_T	$I_C=-10mA, V_{CE}=-5V, f=100MHz$	-	150	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$	-	4.5	-	pF
Noise Figure	NF	$I_C=-200\mu A, V_{CE}=-5V$ $R_g=10k\Omega, f=1kHz$	-	-	4.0	dB

Note : h_{FE} Classification A:125~250, B:220~475

MARK SPEC

TYPE	BC859A	BC859B	BC860A	BC860B
MARK	4A	4B	4E	4G

Marking



BC859/860

